Satoshi Kurai

List of Publications by Year
in descending order

51 papers	840 citations	759233 12 h-index	477307 29 g-index
51 all docs	51 docs citations	51 times ranked	867 citing authors

#	Article	IF	Citations
1	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. Journal of Applied Physics, 2021, 130, 053103.	2.5	0
2	Temperature-dependent cathodoluminescence mapping of InGaN epitaxial layers with different In compositions. Japanese Journal of Applied Physics, 2019, 58, SCCB13.	1.5	0
3	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaN-based multiple quantum wells using rate equations of exciton recombination. Japanese Journal of Applied Physics, 2019, 58, SCCB02.	1.5	11
4	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al_{0.61}Ga_{0.39}N Epitaxial Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700374.	1.5	4
5	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	1.5	13
6	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Nearâ€Field Optical Microscopy. Physica Status Solidi (B): Basic Research, 2018, 255, 1700322.	1.5	3
7	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	1.5	13
8	Nanoscopic spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	2.5	7
9	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaN/AlGaN multiple quantum wells. Japanese Journal of Applied Physics, 2018, 57, 060311.	1.5	2
10	Microscopic potential fluctuations in Si-doped AlGaN epitaxial layers with various AlN molar fractions and Si concentrations. Journal of Applied Physics, 2016, 119, .	2.5	5
11	Image quality of a novel light-emitting diode (LED)-illuminated colonoscope. Endoscopy, 2016, 48, 934-938.	1.8	4
12	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
13	Si concentration dependence of structural inhomogeneities in Si-doped AlxGa1â^'xN/AlyGa1â^'yN multiple quantum well structures (xâ€‰=â€‰0.6) and its relationship with internal quantum efficiency. Journal of Applied Physics, 2014, 116, .	2.5	5
14	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGaN Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JL07.	1.5	6
15	In vitrobactericidal effects of near-ultraviolet light from light-emitting diodes onHelicobacter pylori. Scandinavian Journal of Gastroenterology, 2013, 48, 1484-1486.	1.5	3
16	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. Journal of Applied Physics, 2012, 112, 033512.	2.5	8
17	A novel colonoscope with high colorâ€“rendering white lightâ€“emitting diodes. Gastrointestinal Endoscopy, 2011, 73, 598-602.	1.0	6
18	Recombination dynamics of localized excitons in AlxGa1-xN (0.37<x<0.81) ternary alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2133-2135.	0.8	6

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19	Effect of Package Density on Luminous Efficiency of Direct Flip-Chip Bonded LED for the Phosphor Conversion Lighting. Journal of Japan Institute of Electronics Packaging, 2010, 13, 58-62.	0.1	0
20	A novel imaging system of optical detection on cancers and tissues in gastrointestinal endoscope using high-color-rendering white and color tunable LEDs. Proceedings of SPIE, 2010, , .	0.8	0
21	Study on the Luminous and Thermal Characteristics of High-Power Near-Ultraviolet LED Packages with Various Chip Arrangements. Journal of Light and Visual Environment, 2009, 33, 142-146.	0.2	3
22	Superior Illuminant Characteristics of Color Rendering and Luminous Efficacy in Multilayered Phosphor Conversion White Light Sources Excited by Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2009, 48, 112101.	1.5	41
23	Dependence of Light Extraction From Near-Ultraviolet Light-Emitting Diodes on Refraction Index, Transmittance and Shape. Journal of Light and Visual Environment, 2009, 33, 137-141.	0.2	2
24	Evaluation on Reliability of White LED Light Source Directly Flip-Chip Bonded on Ceramic Substrates. Journal of Japan Institute of Electronics Packaging, 2009, 12, 72-78.	0.1	1
25	Development of White Light Emitting Diodes by Multi-layered Red, Green, and Blue Phosphors Excited by Near-ultraviolet Light Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 43-45.	0.2	11
26	Analysis of Chip/Bump/Ceramic Interface of Flip-Chip Bonded LED Directly on Ceramic Packages. Journal of Light and Visual Environment, 2008, 32, 234-237.	0.2	1
27	Near-ultraviolet LED of the External Quantum Efficiency Over 45% and its Application to High-color Rendering Phosphor Conversion White LEDs. Journal of Light and Visual Environment, 2008, 32, 39-42.	0.2	15
28	Development of Light Sources by Large-Scale Integrated Light-Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 238-240.	0.2	2
29	Growth and Luminescence Properties of Subsequently Grown AlInN Layers on AlN Homoepitaxial Layers by Ammonia Gas Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 3394-3396.	1.5	8
30	Growth and optical properties of AlN homoepitaxial layers grown by ammonia-source molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 461-464.	1.5	9
31	Fabrication and Illuminance Properties of Phosphor-conversion Green Light-emitting Diode with a Luminous Efficacy over 100 lm/W. Journal of Light and Visual Environment, 2007, 31, 146-148.	0.2	8
32	Optical Properties of ZnCdS:I Orange and ZnSTe:I White Thin Film Phosphor for High Ra White LED. Journal of Light and Visual Environment, 2007, 31, 61-64.	0.2	1
33	Homoepitaxial Growth of GaN Layers by Reactive Molecular-Beam Epitaxy on Bulk GaN Single Crystals Prepared by Pressure-Controlled Solution Growth. Japanese Journal of Applied Physics, 2004, 43, 7454-7457.	1.5	2
34	Growth of homoepitaxial GaN layers and GaN/AlGaN multiple quantum wells on GaN single-crystal substrates by molecular-beam epitaxy. , 2002, 4776, 97.		2
35	Pre-treatment of GaN template for homoepitaxial growth by radio-frequency molecular beam epitaxy. Journal of Crystal Growth, 2002, 236, 66-70.	1.5	2
36	Effect of Cooling Process after GaN Epitaxial Growth by Radio-Frequency Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, L1297-L1300.	1.5	3

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37	Defect identification in homoepitaxial- and ELO-grown GaN layers using bound-exciton Zeeman spectroscopies. Journal of Crystal Growth, 2000, 210, 216-219.	1.5	0
38	Homoepitaxial growth of GaN thin layer by molecular beam epitaxy with an RF nitrogen plasma. Vacuum, 2000, 59, 277-283.	3.5	4
39	Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method. Japanese Journal of Applied Physics, 2000, 39, 2394-2398.	1.5	16
40	Effect of pre-treatment of GaN substrate for homoepitaxial growth by rf MBE. , 2000, , .		0
41	Excitonic Emissions under High Excitation of Hexagonal GaN Single Crystal Grown by Sublimation Method. Japanese Journal of Applied Physics, 1999, 38, L102-L104.	1.5	11
42	Time-resolved spectroscopy of excitonic luminescence from GaN homoepitaxial layers. Journal of Applied Physics, 1999, 86, 7186-7188.	2.5	13
43	Direct Evidence that Dislocations are Non-Radiative Recombination Centers in GaN. Japanese Journal of Applied Physics, 1998, 37, L398-L400.	1.5	417
44	Correlation between dislocations and luminescence in GaN. , 1998, , .		1
45	Surface Pretreatment of Bulk GaN for Homoepitaxial Growth by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 626-631.	1.5	11
46	Nucleation Control in the Growth of Bulk GaN by Sublimation Method. Japanese Journal of Applied Physics, 1997, 36, L184-L186.	1.5	29
47	Growth of GaN by Sublimation Technique and Homoepitaxial Growth by MOCVD. Materials Research Society Symposia Proceedings, 1996, 449, 15.	0.1	12
48	Photopumped Stimulated Emission from Homoepitaxial GaN Grown on Bulk GaN Prepared by Sublimation Method. Japanese Journal of Applied Physics, 1996, 35, L77-L79.	1.5	69
49	Growth and Characterization of Thick GaN by Sublimation Method and Homoepitaxial Growth by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, 1637-1640.	1.5	26
50	Transmission Electron Microscopy of Sublimation-Grown GaN Single Crystal and GaN Homoepitaxial Film. Japanese Journal of Applied Physics, 1996, 35, L1318-L1320.	1.5	3
51	Stress distribution and dislocation dynamics in GaAs grown on Si by metalorganic chemical vapor deposition. Journal of Crystal Growth, 1994, 145, 321-325.	1.5	0